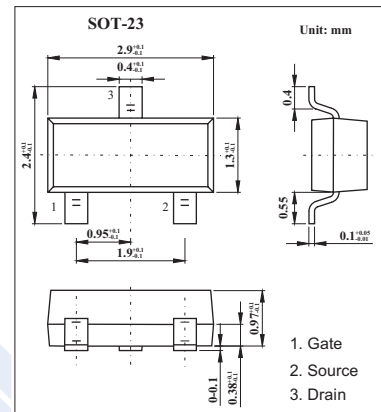
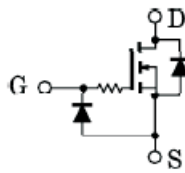


MOS Field Effect Transistor

2SK2033

■ Features

- High input impedance.
- Low gate threshold voltage : $V_{th}=0.5$ to $1.5V$
- Enhancement-Mode



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DS}	20	V
Gate to source voltage	V_{GS}	10	V
Drain current	I_D	100	mA
Power dissipation	P_D	200	mW
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=10V, V_{GS}=0$			1	μA
Gate leakage current	I_{GSS}	$V_{GS}=20V, V_{DS}=0$			1	μA
Gate threshold voltage	V_{th}	$V_{DS}=3V, I_D=0.1mA$	0.5		1.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=3V, I_D=10mA$	25	50		ms
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=2.5V, I_D=10mA$		8	12	Ω
Input capacitance	C_{iss}	$V_{DS}=3V, V_{GS}=0, f=1MHz$		8.5		pF
Output capacitance	C_{oss}			3.3		pF
Reverse transfer capacitance	C_{rss}			9.3		pF
Turn-on delay time	$t_{d(on)}$	$I_D=10mA, V_{GS(on)}=2.5V, V_{DD}=3V$		0.16		μs
Turn-off delay time	$t_{d(off)}$			0.15		μs

■ Marking

Marking	KP
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